

isc N-Channel MOSFET Transistor

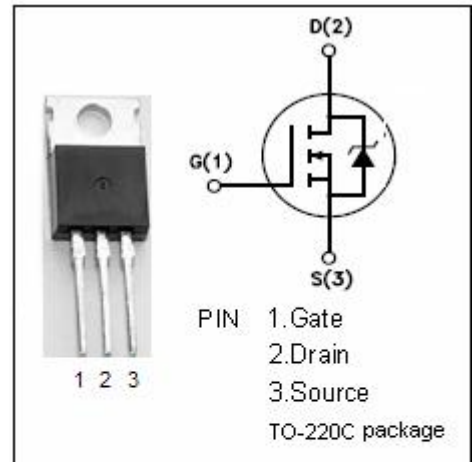
BUK455-200A/B

DESCRIPTION

- High speed switching

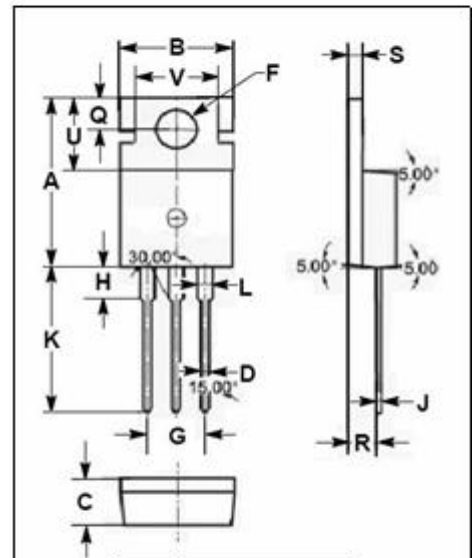
APPLICATIONS

- use in Switched Mode Power Supplies (SMPS), motor control, welding, And in general purpose switching resistance application



ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	ARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage (V _{GS} =0)	200	V
V _{GS}	Gate-Source Voltage	±30	V
I _D	Drain Current-continuous @ TC=37°C	BUK455-200A	14
		BUK455-200B	13
P _{tot}	Total Dissipation@TC=25°C	125	W
T _j	Max. Operating Junction Temperature	175	°C
T _{stg}	Storage Temperature Range	175	°C



DIM	mm	
	MIN	MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance,Junction to Case	1.2	°C/W
R _{th j-a}	Thermal Resistance,Junction to Ambient	60	°C/W

isc N-Channel Mosfet Transistor**BUK455-200A/B****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 0.25mA	200		V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 1mA	2.1	4	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 10V; I _D = 7A		0.23	Ω
		BUK455-200A		0.28	
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±30V; V _{DS} = 0		±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 200V; V _{GS} = 0		10	uA
V _{SD}	Diode Forward Voltage	I _F = 14A; V _{GS} = 0		1.5	V